

# PSMN4R0-60YS

N-channel LFPAK 60 V, 4.0 mΩ standard level FET

14 May 2015 Product data sheet

# 1. General description

Standard level N-channel MOSFET in LFPAK package qualified to 175 °C. This product is designed and qualified for use in a wide range of telecom, industrial and domestic equipment.

#### 2. Features and benefits

- Advanced TrenchMOS provides low R<sub>DSon</sub> and low gate charge
- High efficiency in switching power converters
- Improved mechanical and thermal characteristics
- LFPAK provides maximum power density in a Power SO8 package

### 3. Applications

- DC-to-DC converters
- Lithium-ion battery protection
- Load switching
- Motor control
- Server power supplies
- Telecom power

#### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	-	60	V
I <sub>D</sub>	drain current	T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>	[1]	-	-	100	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>		-	-	130	W
T <sub>j</sub>	junction temperature			-55	-	175	°C
Static charact	eristics						
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 15 A; T <sub>j</sub> = 100 °C; Fig. 12		-	-	8.3	mΩ
		$V_{GS}$ = 10 V; $I_D$ = 15 A; $T_j$ = 25 °C; Fig. 13		-	3.6	4	mΩ



Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Dynamic cha	Dynamic characteristics						
$Q_{GD}$	gate-drain charge	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 75 A; V <sub>DS</sub> = 30 V;		-	11.2	-	nC
Q <sub>G(tot)</sub>	total gate charge	Fig. 14; Fig. 15		-	56	-	nC
Avalanche ru	ggedness		1		'		
E <sub>DS(AL)S</sub>	non-repetitive drain- source avalanche energy	$V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; $I_{D}$ = 100 A; $V_{sup}$ ≤ 60 V; $R_{GS}$ = 50 Ω; unclamped		-	-	170	mJ

[1] Continuous current is limited by package.

# 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	mb	D
2	S	source		
3	S	source	d j	G T A
4	G	gate	<u> </u>	mbb076 S
mb	D	mounting base; connected to drain	1 2 3 4 LFPAK56; Power- SO8 (SOT669)	

# 6. Ordering information

Table 3. Ordering information

Table 6. Grading III	ioimation					
Type number	Package					
	Name	Description	Version			
PSMN4R0-60YS	LFPAK56; Power-SO8	Plastic single-ended surface-mounted package (LFPAK56; Power-SO8); 4 leads	SOT669			

# 7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C	-	60	V
$V_{DGR}$	drain-gate voltage	$T_j \ge 25$ °C; $T_j \le 175$ °C; $R_{GS} = 20$ kΩ	-	60	V
$V_{GS}$	gate-source voltage		-20	20	V
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>	-	130	W
I <sub>D</sub>	drain current	T <sub>mb</sub> = 100 °C; <u>Fig. 2</u>	-	74	Α

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Symbol	Parameter	Conditions		Min	Max	Unit
		T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>	[1]	-	100	Α
I <sub>DM</sub>	peak drain current	pulsed; $t_p \le 10 \mu s$ ; $T_{mb} = 25 °C$ ; Fig. 3		-	418	Α
T <sub>stg</sub>	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
T <sub>sld(M)</sub>	peak soldering temperature			-	260	°C
Source-dra	in diode		•			
I <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C	[1]	-	100	Α
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$		-	418	Α
Avalanche	ruggedness					
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; $I_{D}$ = 100 A; $V_{sup} \le$ 60 V; $R_{GS}$ = 50 Ω; unclamped		-	170	mJ

#### [1] Continuous current is limited by package.

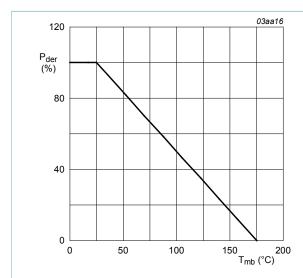


Fig. 1. Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

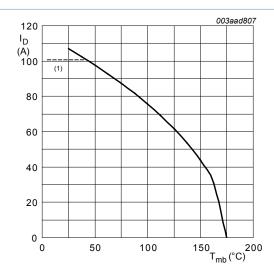


Fig. 2. Continuous drain current as a function of mounting base temperature

 $V_{GS} \geq 10 \text{ V}$ ; (1) capped at 100 A due to package

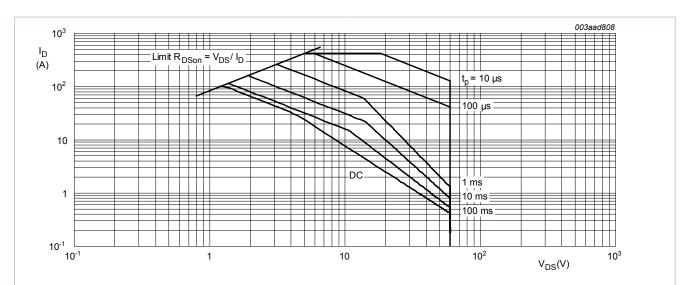


Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

 $T_{mb} = 25$  °C;  $I_{DM}$  is a single pulse

#### 8. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	Fig. 4	-	0.5	1.1	K/W

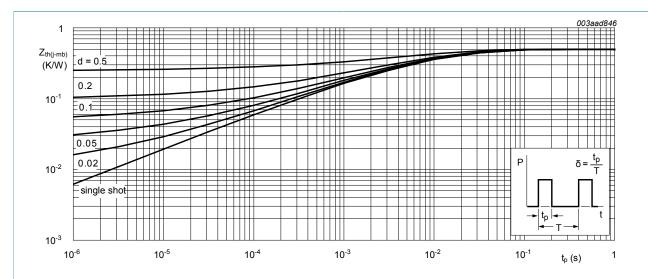


Fig. 4. Transient thermal impedance from junction to mounting base as a function of pulse duration; typical values

## 9. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	cteristics					
V <sub>(BR)DSS</sub>	drain-source	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 °C$	54	-	-	V
	breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	63	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	I <sub>D</sub> = 1 mA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>j</sub> = 25 °C; Fig. 10; Fig. 11	2	3	4	V
$V_{GSth}$	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ Fig. 11	-	-	4.6	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C};$ Fig. 11	0.95	-	-	V
I <sub>DSS</sub>	drain leakage current	$V_{DS} = 60 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.05	5	μA
		V <sub>DS</sub> = 63 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	0.07	7	μA
		V <sub>DS</sub> = 60 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 125 °C	-	-	100	μA
		V <sub>DS</sub> = 63 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 125 °C	-	3.25	150	μA
I <sub>GSS</sub> ga	gate leakage current	V <sub>GS</sub> = 20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	2	100	nA
		V <sub>GS</sub> = -20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	2	100	nA
Doon	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A}; T_j = 175 \text{ °C};$ Fig. 12	-	7.6	12	mΩ
		$V_{GS}$ = 10 V; $I_D$ = 15 A; $T_j$ = 100 °C; Fig. 12	-	-	8.3	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A}; T_j = 25 ^{\circ}\text{C};$ Fig. 13	-	3.6	4	mΩ
$R_{G}$	gate resistance	f = 1 MHz	-	0.7	-	Ω
Dynamic ch	aracteristics	1			-1	
Q <sub>G(tot)</sub>	total gate charge	I <sub>D</sub> = 75 A; V <sub>DS</sub> = 30 V; V <sub>GS</sub> = 10 V; Fig. 14; Fig. 15	-	56	-	nC
		I <sub>D</sub> = 0 A; V <sub>DS</sub> = 0 V; V <sub>GS</sub> = 10 V	-	47.5	-	nC
Q <sub>GS</sub>	gate-source charge	I <sub>D</sub> = 75 A; V <sub>DS</sub> = 30 V; V <sub>GS</sub> = 10 V; Fig. 14; Fig. 15	-	18.7	-	nC
Q <sub>GS(th)</sub>	pre-threshold gate- source charge	I <sub>D</sub> = 75 A; V <sub>DS</sub> = 30 V; V <sub>GS</sub> = 10 V; Fig. 14	-	10.3	-	nC
Q <sub>GS(th-pl)</sub>	post-threshold gate- source charge		-	8.4	-	nC
$Q_GD$	gate-drain charge	I <sub>D</sub> = 75 A; V <sub>DS</sub> = 30 V; V <sub>GS</sub> = 10 V; Fig. 14; Fig. 15	-	11.2	-	nC
V <sub>GS(pl)</sub>	gate-source plateau voltage	V <sub>DS</sub> = 30 V; <u>Fig. 14</u> ; <u>Fig. 15</u>	-	4.9	-	V

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Symbol	Parameter	Conditions		Min	Тур	Max	Unit
C <sub>iss</sub>	input capacitance	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$		-	3501	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C; <u>Fig. 16</u>		-	457	-	pF
C <sub>rss</sub>	reverse transfer capacitance			-	240	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = 30 V; $R_{L}$ = 0.4 $\Omega$ ; $V_{GS}$ = 10 V; $R_{G(ext)}$ = 4.7 $\Omega$		-	23	-	ns
t <sub>r</sub>	rise time			-	24	-	ns
$t_{d(off)}$	turn-off delay time	_		-	44	-	ns
t <sub>f</sub>	fall time	1		-	14	-	ns
Source-dra	ain diode						
V <sub>SD</sub>	source-drain voltage	$I_S = 15 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}; Fig. 17$		-	8.0	1.2	V
t <sub>rr</sub>	reverse recovery time	$I_S$ = 25 A; $dI_S/dt$ = -100 A/ $\mu$ s; $V_{GS}$ = 0 V; $V_{DS}$ = 30 V		-	43	-	ns
Q <sub>r</sub>	recovered charge			-	58	-	nC

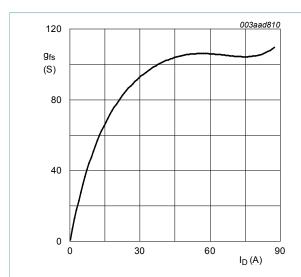


Fig. 5. Forward transconductance as a function of drain current; typical values

$$T_j$$
 = 25 °C;  $V_{DS}$  = 15 V

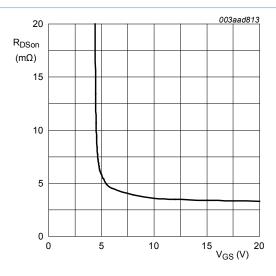


Fig. 6. Drain-source on-state resistance as a function of gate-source voltage; typical values

$$T_j = 25$$
 °C;  $I_D = 25$  A

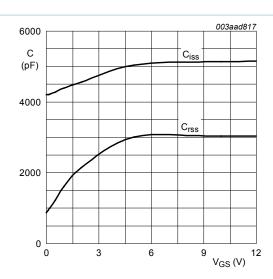


Fig. 7. Input and reverse transfer capacitances as a function of gate-source voltage, typical values

$$V_{DS} = 0 \text{ V; } f = 1 \text{ MHz}$$

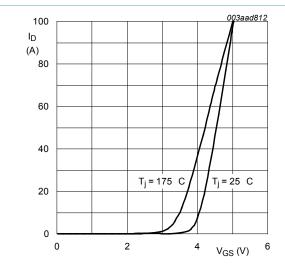


Fig. 9. Transfer characteristics: drain current as a function of gate-source voltage; typical values

$$V_{DS} > I_D \times R_{DSon}$$

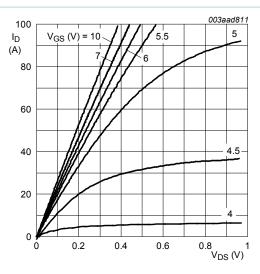


Fig. 8. Output characteristics: drain current as a function of drain-source voltage; typical values

$$T_j=25\,^{\circ}C$$

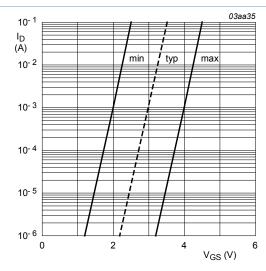


Fig. 10. Sub-threshold drain current as a function of gate-source voltage

$$T_j=25\,^{\circ}C; V_{DS}=5V$$

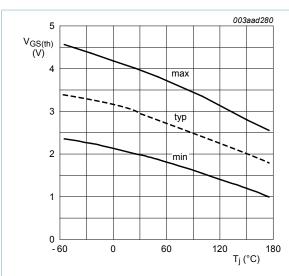


Fig. 11. Gate-source threshold voltage as a function of junction temperature

$$I_D = 1 \text{ mA}; \ V_{DS} = V_{GS}$$

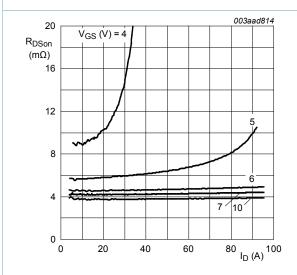


Fig. 13. Drain-source on-state resistance as a function of drain current; typical values

$$T_j = 25 \,^{\circ}C$$

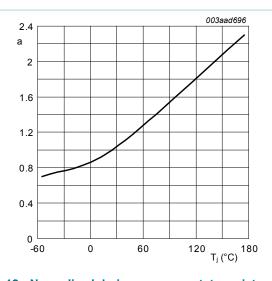


Fig. 12. Normalized drain-source on-state resistance factor as a function of junction temperature.

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

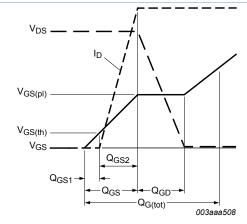


Fig. 14. Gate charge waveform definitions

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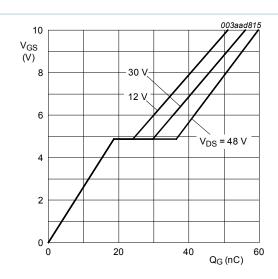


Fig. 15. Gate-source voltage as a function of gate charge; typical values

$$T_J = 25$$
 °C;  $I_D = 75$  A

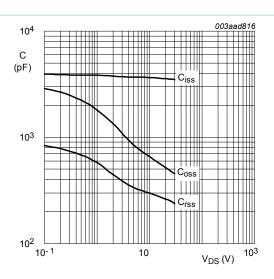


Fig. 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

$$V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}$$

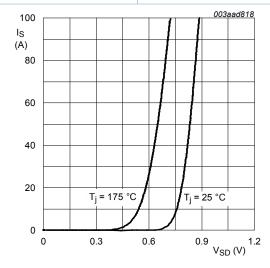
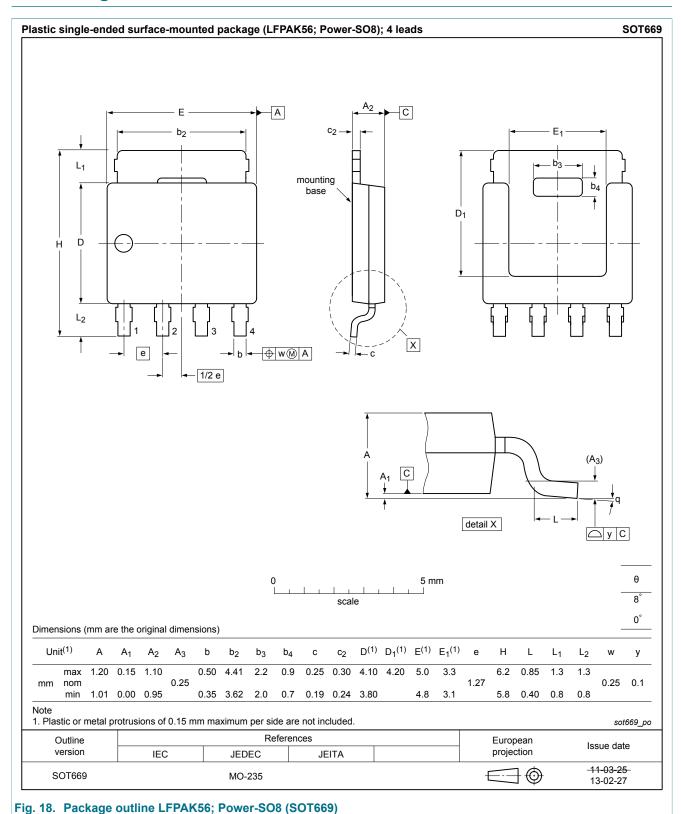


Fig. 17. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

$$V_{GS} = 0 \text{ V}$$

# 10. Package outline



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